

## 30V N-Channel MOSFET

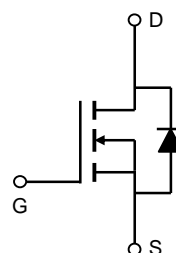
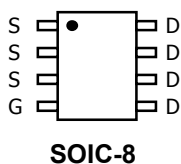
### General Description

The 4420 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , shoot-through immunity and body diode characteristics. This device is suitable for use as a synchronous switch in PWM applications.

### Product Summary

$V_{DS}$  (V) = 30V  
 $I_D$  = 12A ( $V_{GS}$  = 10V)  
 $R_{DS(ON)}$  < 10.5m $\Omega$  ( $V_{GS}$  = 10V)  
 $R_{DS(ON)}$  < 12m $\Omega$  ( $V_{GS}$  = 4.5V)

100% UIS Tested  
 100% Rg Tested



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A</sup>	$I_D$	12	A
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	60	
Power Dissipation	$P_D$	3.1	W
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	28	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>		54	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	21	30	$^\circ\text{C/W}$

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V		0.004	1	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	0.6	1.1	2	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	40			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =12A		8.3	10.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A		9.7	12	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =12A	30	37		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.76	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		3656	4050	pF
C <sub>oss</sub>	Output Capacitance			256		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			168		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		0.86	1.1	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(4.5V)</sub>	Total Gate Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =15V, I <sub>D</sub> =12A		30.5	36	nC
Q <sub>gs</sub>	Gate Source Charge			4.6		nC
Q <sub>gd</sub>	Gate Drain Charge			8.6		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.1Ω, R <sub>GEN</sub> =3Ω		5.5	9	ns
t <sub>r</sub>	Turn-On Rise Time			3.4	7	ns
t <sub>D(off)</sub>	Turn-Off DelayTime			49.8	75	ns
t <sub>f</sub>	Turn-Off Fall Time			5.9	11	ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =12.0A, dI/dt=100A/μs		22.5	28	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =12.0A, dI/dt=100A/μs		12.5	16	nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

Rev 8 : Nov 2010

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

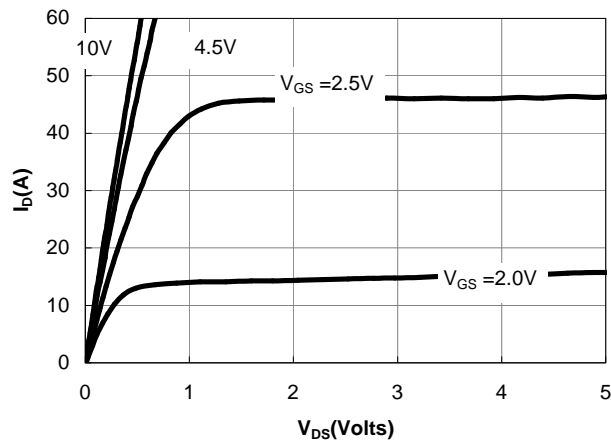


Figure 1: On-Regions Characteristics

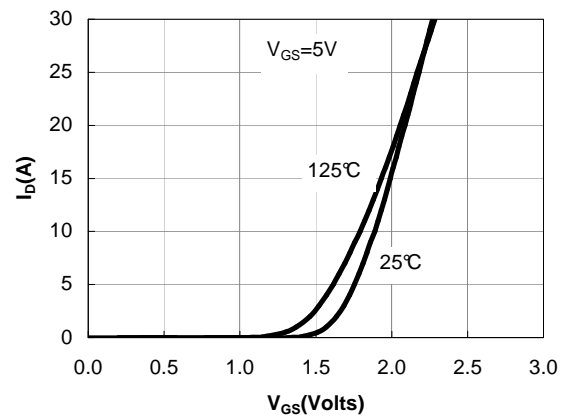


Figure 2: Transfer Characteristics

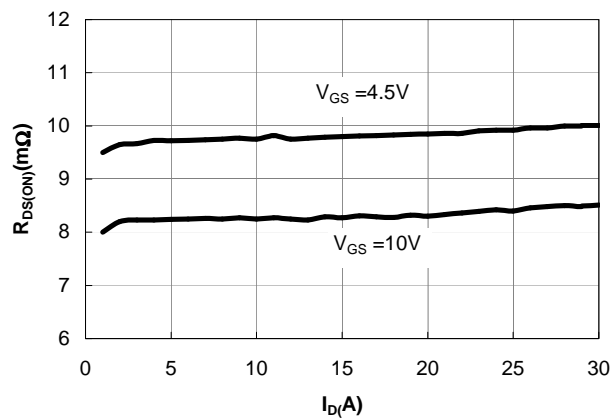


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

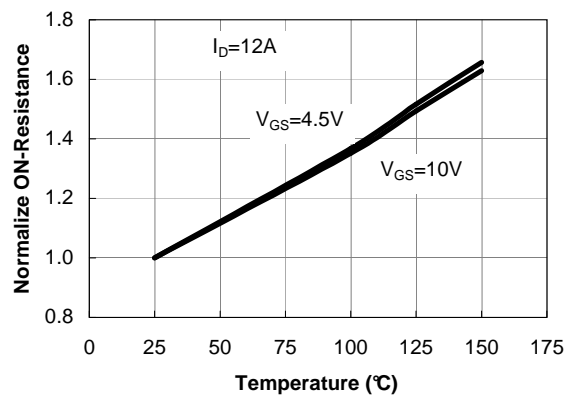


Figure 4: On-Resistance vs. Junction Temperature

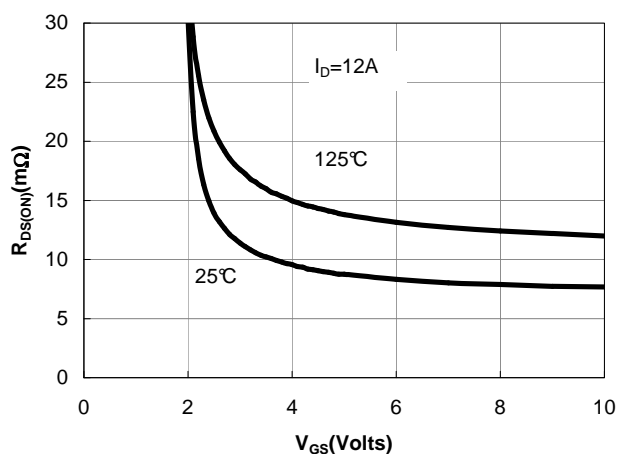


Figure 5: On-Resistance vs. Gate-Source Voltage

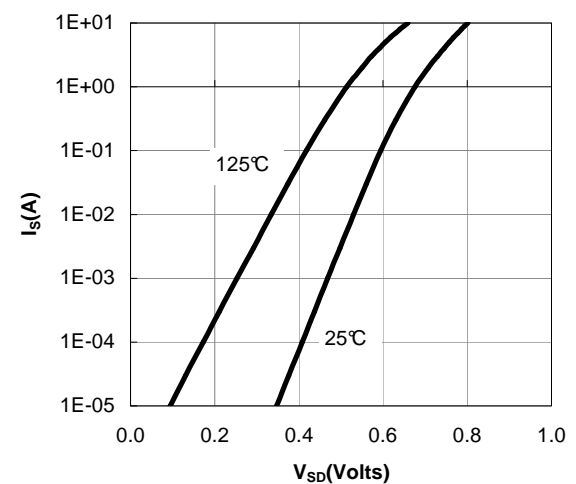


Figure 6: Body-Diode Characteristics

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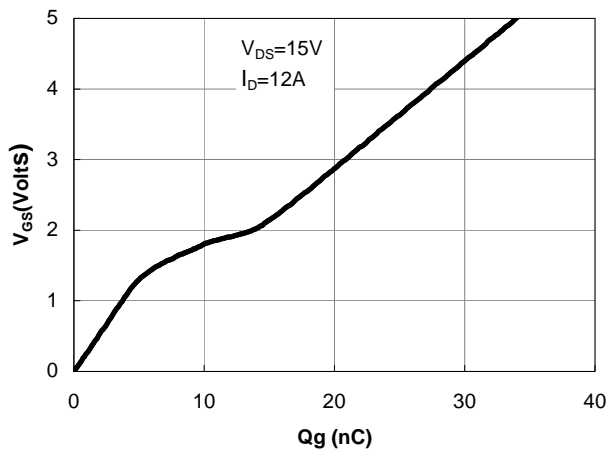


Figure 7: Gate-Charge Characteristics

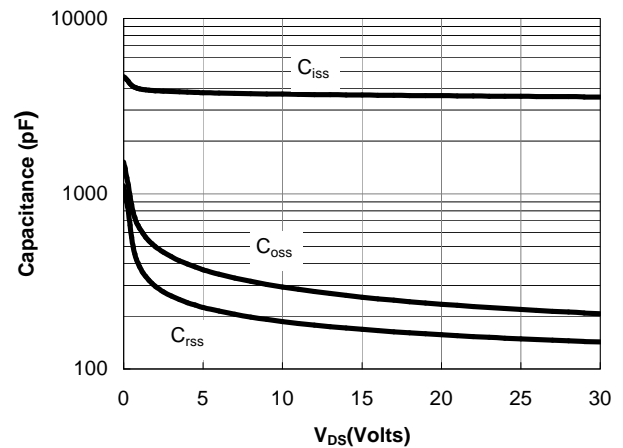


Figure 8: Capacitance Characteristics

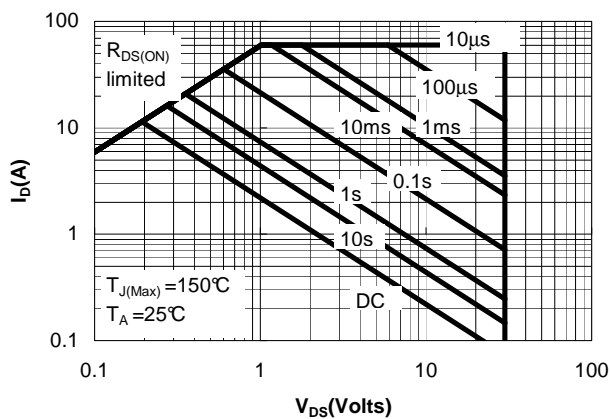


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

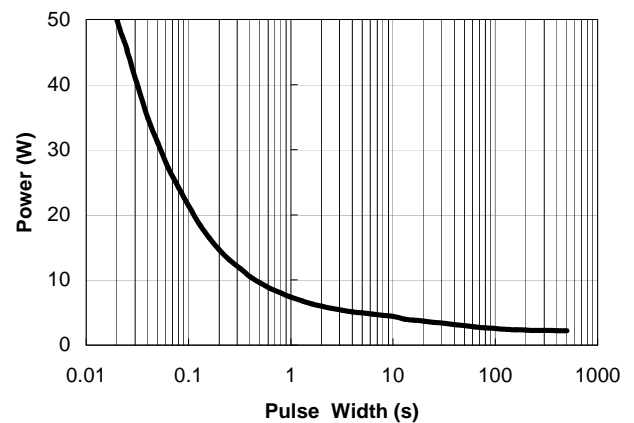


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

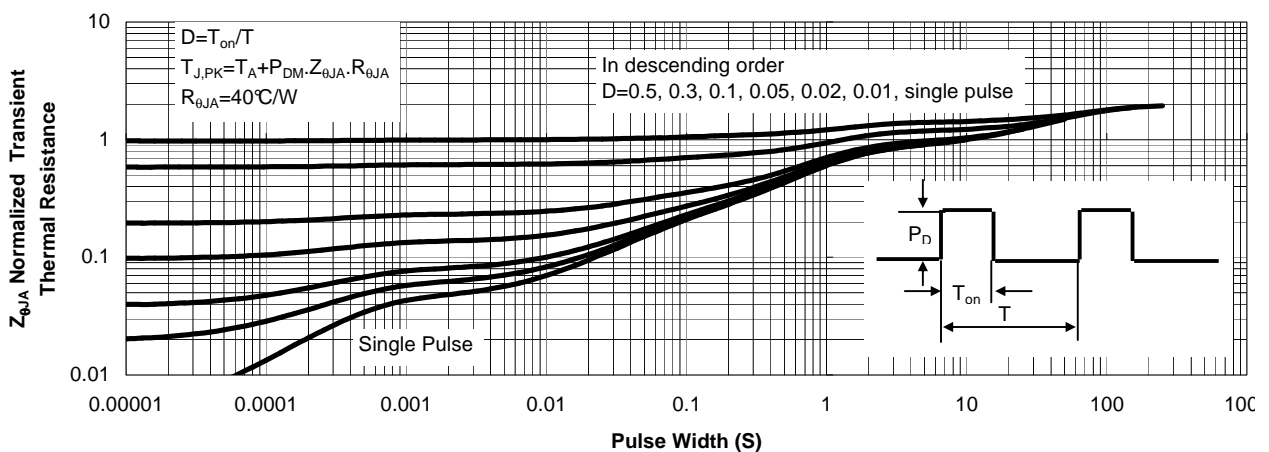


Figure 11: Normalized Maximum Transient Thermal Impedance